# New Jersey Semi-Conductor Products, Inc.

20 STERN AVE. SPRINGFIELD, NEW JERSEY 07081 U.S.A.

**D40C Series** 

30-50 VOLTS .5 AMP, 6.25 WATTS TELEPHONE: (973) 376-2922

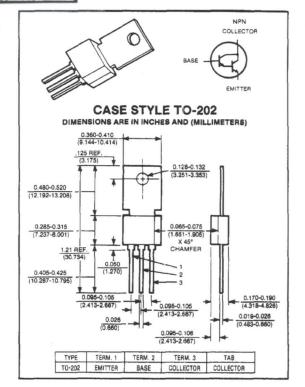
(212) 227-6005

FAX: (973) 376-8960

Designed for driver, regulator, touch switch, I.C. driver, audio output, relay substitute, oscillator, servo-amplifier, and capacitor multiplier applications.

#### Features:

- hFE Min. 10,000 and 40,000
- 1.33 Watt power dissipation at TA = 25°



# maximum ratings (T<sub>A</sub> = 25°C) (unless otherwise specified)

RATING	SYMBOL	D40C1	D40C4	D40C7	UNITS
Collector-Emitter Voltage	VCEO	30	40	50	Volts
Collector-Emitter Voltage	VCES	30	40	50	Volts
Emitter Base Voltage	V <sub>EBO</sub>	13	13	13	Volts
Collector Current — Continuous Peak <sup>(1)</sup>	I <sub>C</sub> M	.5 1.0	.5 1.0	.5 1.0	А
Base Current — Continuous	IB	0.1	0.1	0.1	Α
Total Power Dissipation @ T <sub>A</sub> = 25° C @ T <sub>C</sub> = 25° C	PD	1.33 6.25	1.33 6.25	1.33 6.25	Watts
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	-55 to +150	-55 to +150	°C

### thermal characteristics

Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	75	75	75	°C/W
Thermal Resistance, Junction to Case	R <sub>€JC</sub>	20	20	20	°C/W
Maximum Lead Temperature for Soldering Purposes: '%" from Case for 5 Seconds	TL	260	260	260	°C

Pulse Test: Pulse Width = 300ms. Duty Cycle ≤ 2%.

NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors

# electrical characteristics ( $T_C = 25^{\circ}C$ ) (unless otherwise specified)

CHARACTERISTIC		SYMBOL	MIN	TYP	MAX	UNIT
off characteristics <sup>(1)</sup>						
Collector-Emitter Voltage (I <sub>C</sub> = 10mA)	D40C1 D40C4 D40C7	VCEO	30 40 50	=	=	Volts
Collector Cut-off Current (VCE = Rated VCES)	(T <sub>C</sub> = 25°C) (T <sub>C</sub> = 150°C)	ICES ICBO	_	=	0.5 20	μА
Emitter Cutoff Current (V <sub>EB</sub> = 13V)		IEBO	_	_	0.1	μΑ

### second breakdown

Second Breakdown with Base Forward Biased	FBSOA	SEE FIGURE 2

### on characteristics

DC Current Gain (I <sub>C</sub> = 200mA, V <sub>CE</sub> = 5V)	hFE	10K	_	60K	
Collector-Emitter Saturation Voltage (I <sub>C</sub> = 500mA, I <sub>B</sub> = 0.5mA)	V <sub>CE(sat)</sub>	_	_	1.5	V
Base-Emitter Saturation Voltage (I <sub>C</sub> = 500mA, I <sub>B</sub> = 0.5mA)	V <sub>BE(sat)</sub>	_	_	2.0	Volts

## dynamic characteristics

Collector Capacitance (V <sub>CE</sub> = 10V, f = 1MHz)	ССВО	_	_	220	pF
Current Gain - Bandwidth Product (I <sub>C</sub> = 20mA, V <sub>CE</sub> = 5V)	f <sub>T</sub>	_	75	_	MHz

### switching characteristics

Resistive Load						
Delay Time + Rise Time	I <sub>C</sub> = 1A, I <sub>B1</sub> = I <sub>B2</sub> = 1mA	td + tr	_	100	_	ns
Storage Time	$V_{CC}$ = 30V, $t_p$ = 25 $\mu$ sec	ts	_	350	_	
Fall Time		t <sub>f</sub>		800	_	

<sup>(1)</sup> Pulse Test: PW ≤ 300ms Duty Cycle ≤ 2%.

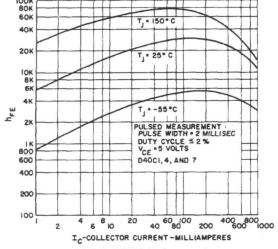


FIG 1. TYPICAL hpe vs. IC

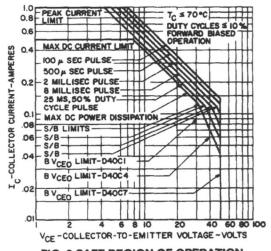


FIG. 2 SAFE REGION OF OPERATION